



**Mechanical data:**  $A_x=A_y=210\mu\text{m}$   
 $B_x=B_y=85\mu\text{m}$

**Schematic and pinning diagram**

**Chip thickness:**  $635 \pm 20\mu\text{m}$

**Scribe Line width** -  $40\mu\text{m}$ .

**Top Metal:** Ti-Ni-Ag for Soldering.

**Back side** : without metallization

**Top Side** - pin 1, **Back Side** - pin 2.

**Probing: sampling testing:** no bad dice inking, guaranteed good dice quantity  $\geq 95\%$ .

### Limiting values

Parameter	Symbol	Conditions	Value	Unit
Working Peak Reverse Voltage	$V_{RWM}$		5,0.	V
Peak Pulse Power	$P_{pp}$	$t_p = 8/20\mu\text{s}$	60*	W
Peak Pulse Current	$I_{pp}$	$t_p = 8/20\mu\text{s}$	3,0*	A
Electrostatic Discharge	$V_{ESD}$	IEC 61000-4-2, level 4.	+/-10,0 (Contact); +/-15,0 (Air).	kV
Max.junction temperature	$T_j$		+150	°C

### Characteristics ( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_R$	Diode reverse leakage current.	$V = \pm 5 \text{ V}$	-	-	100	nA
$V_{BR}$	Breakdown voltage. Pin1 to 2 and Pin 2 to 1	$I_R = 1\text{mA}$	5,6	-	9,4	V
$C_j$	Diode capacitance .	$f = 1\text{MHz}, V_{dc} = 0 \text{ V}$ .	8,0	10	13,0	pF
$V_{CL}$	Clamping Voltage	$I_{pp} = 1,0\text{A};$ $I_{pp} = 3,0\text{A};$ $t_p = 8/20\mu\text{s} .$	-	-	12,0* 20,0*	V

\*- For Device testing